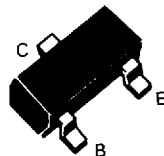


SOT23 NPN SILICON PLANAR HIGH VOLTAGE TRANSISTOR

BSS64

* COMPLEMENTARY TYPE - BSS63

PARTMARKING DETAILS - BSS64 = U3
BSS64R = U6



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	100	mA
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{TOT}	330	mW
Operating and Storage Temperature Range	$t_j:tstg$	- 55 to + 150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	120		V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80		V	$I_C = 4\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		V	$I_E = 100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		100 50	nA μA	$V_{CB} = 90\text{V}$ $V_{CB} = 90\text{V}, T_j = 150^\circ\text{C}$
Emitter Cut-Off Current	I_{EBO}		200	nA	$V_{EB} = 5\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$		150 200	mV mV	$I_C = 4\text{mA}, I_B = 400\mu\text{A}$ $I_C = 50\text{mA}, I_B = 15\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$		1.2	V	$I_C = 4\text{mA}, I_B = 400\mu\text{A}$
Static Forward Current	h_{FE}	20	Typ. 60 80 55		$I_C = 1\text{mA}, V_{CE} = -1\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1\text{V}$ $I_C = 20\text{mA}, V_{CE} = 1\text{V}$
Transition Frequency	f_T	60	Typ. 100	MHz	$V_{CE} = 10\text{V}, I_C = 4\text{mA}$ $f = 35\text{ MHz}$
Output Capacitance	C_{obo}	Typ. 3	5	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$

* Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle = $\leq 2\%$

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